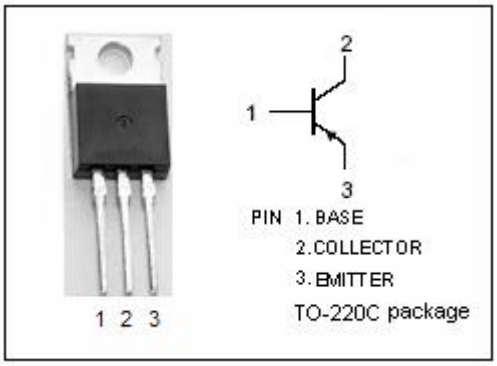
isc Silicon PNP Power Transistors — TIP32A



DESCRIPTION

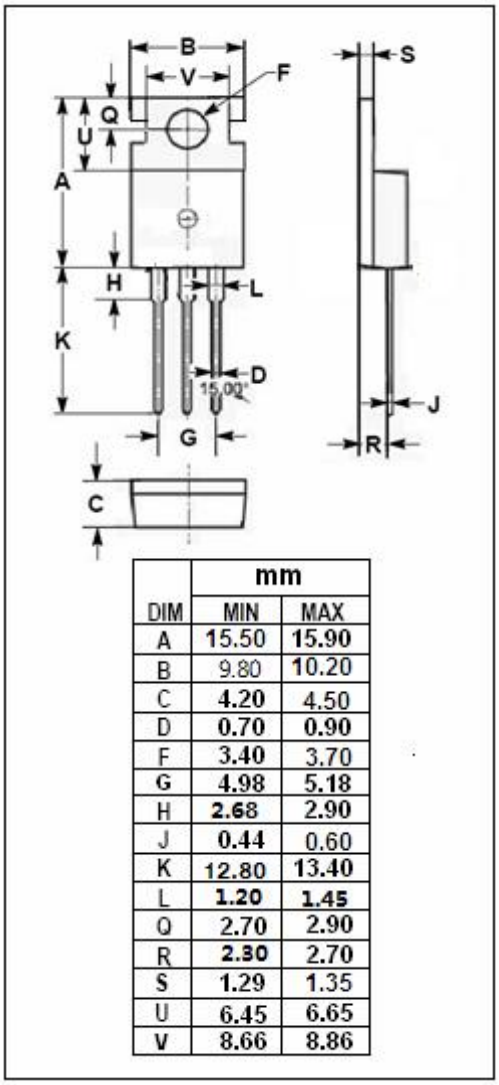
- DC Current Gain -h_{FE} = 25(Min)@ I_C= -1.0A
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = -60V(Min)
- Complement to Type TIP31A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in general purpose amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-base Voltage	-60	V
V_{CEO}	Collector-emitter Voltage	-60	V
V_{EBO}	Emitter-base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Pulse	-5	A
I_B	Base Current	-1	A
P_C	Collector Power Dissipation T_C=25℃	40	W
	Collector Power Dissipation T_a=25℃	2	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Ttemperature Range	-65~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon PNP Power Transistors TIP32A

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA; I_B= 0	-60		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.375A		-1.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -3A ; V_{CE}= -4V		-1.8	V
I_{CES}	Collector Cutoff Current	V_{CE}= -60V; V_{EB}= 0		-0.2	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= -30V; I_B= 0		-0.3	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-1.0	mA
h_{FE-1}	DC Current Gain	I_C= -1A ; V_{CE}= -4V	25		
h_{FE-2}	DC Current Gain	I_C= -3A ; V_{CE}= -4V	10	50	
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A ; V_{CE}= -10V	3		MHz